

Crossbar RRAM

A New Era of Storage Innovation for a Content Rich World Wei Lu Chief Scientist and co-founder, Crossbar

Santa Clara, CA August 2016







Crossbar-1 Advantages for IoT Applications

Byte write in **12us 0** block erase required Read in **25ns** Embedded macros and stand-alone chips

Available at 40nm, scalable below 10nm

Cell size not constrained by RRAM, scales with select transistor Fewer process steps and masks vs eFlash

RRA

-40/150C support withstands solder reflow
Operating voltage below 2V
No high-voltage forming process required
10 year retention

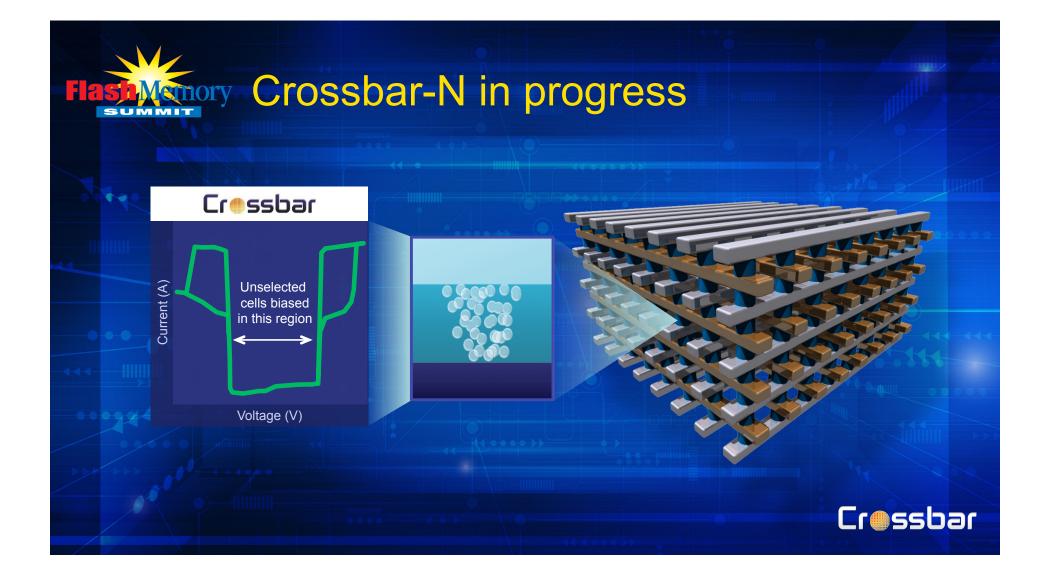
100k cycles

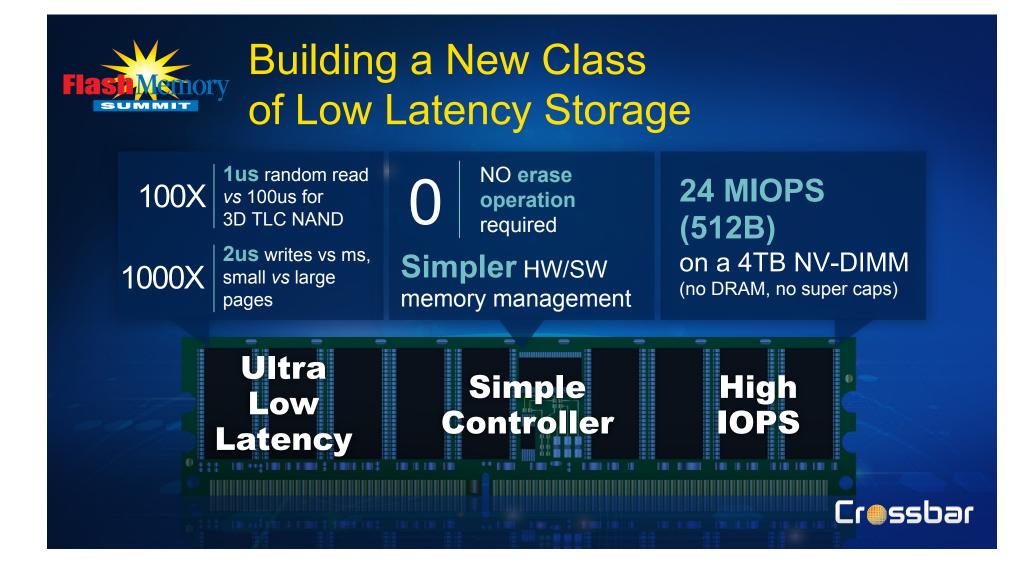
Fast

Scalable

Reliable

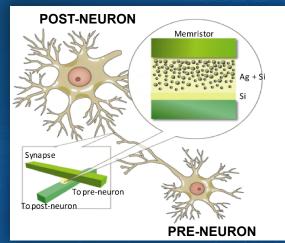
Cressbar



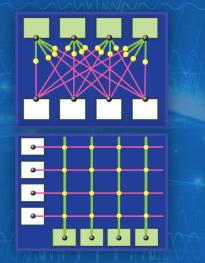




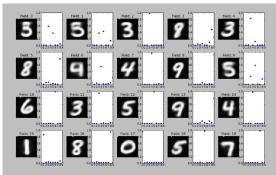
Building RRAM Based Neural Networks



S. H. Jo, T. Chang, I. Ebong, B. Bhavitavya, P. Mazumder, W. Lu, Nano Lett. 10, 1297-1301 (2010).



UNSUPERVISED LEARNING WITH TASK-DRIVEN DICTIONARY



Receptive Fields (28x28) Random sample of 20 from 50 output neurons

Crossbar Embedded RRAM enabling post Von Neumann architecture processing machines





Crossbar Corporate Facts

At A Glance

- Founded in 2010. Based in Santa Clara, CA
- Leader in Resistive RAM technology
- Path to commercialization:
 - Crossbar-1 Embedded Memory
 - IP Licensing in SoC and MCUs
 - Crossbar-N Storage Solutions
 - IP Licensing, IC and systems

Patented Technology

- New class of Non-Volatile Memory:
 - Fast, Low Latency
 - Scalable, 3D, MLC
 - Dense
 - Embedded, CMOS compatible
- 210 filed
- **108 issued** by Crossbar + exclusive license to University of Michigan's RRAM inventions





Thank You

Cr@ssbar